

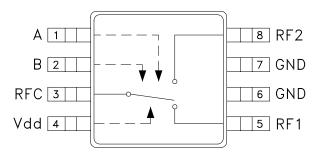
GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

Typical Applications

The HMC574AMS8E is ideal for:

- Cellular/3G Infrastructure
- Private Mobile Radio Handsets
- WLAN, WiMAX & WiBro
- Automotive Telematics
- Test Equipment

Functional Diagram



Features

Low Insertion Loss: 0.3 dB

High Third Order Intercept: +63 dBm

Isolation: 30 dB

Single Positive Supply: +3 to +8V

SMT Package: MSOP8

General Description

The HMC574AMS8E is low-cost SPDT switch in 8-lead MSOP packages for use in transmit/receive applications which requires very low distortion at high incident power levels. The device can control signals from DC to 3 GHz and is especially suited for Cellular/3G infrastructure, WiMAX and WiBro applications with only 0.3 dB typical insertion loss. The design provides 5 watt power handling performance and +63 dBm third order intercept at +8 Volt bias. RF1 and RF2 are reflective shorts when "Off".

Electrical Specifications,

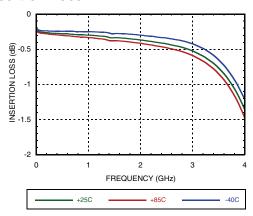
 $T_A = +25^{\circ}$ C, VctI = 0/+5 Vdc, Vdd = +5 Vdc (Unless Otherwise Stated), 50 Ohm System

Parai	meter	Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		0.25 0.3 0.4 0.5	0.5 0.6 0.7 0.8	dB dB dB dB
Isolation		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz	26 24 21 16	30 28 25 20		dB dB dB dB
Return Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		35 30 25 22		dB dB dB dB
Input Power for 1dB Compression	Vctl = 0/+3V Vctl = 0/+5V Vctl = 0/+8V	0.5 - 3.0 GHz	31 35 37	34 38 39		dBm dBm dBm
Input Third Order Intercept P _{tone} = Two-tone Input Power (Each Tone)	$ \begin{array}{l} {\rm VctI} = {\rm O}/{\rm + 3V}, {\rm P_{tone}} = +23 \; {\rm dBm} \\ {\rm VctI} = {\rm O}/{\rm + 5V}, {\rm P_{tone}} = +27 \; {\rm dBm} \\ {\rm VctI} = {\rm O}/{\rm + 8V}, {\rm P_{tone}} = +27 \; {\rm dBm} \\ \end{array} $	0.5 - 3.0 GHz		63 63 63		dBm dBm dBm
Switching Characteristics		DC - 3.0 GHz				
	tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)			40 70		ns ns

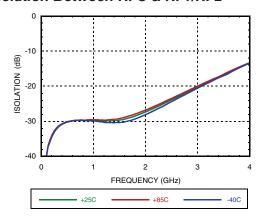


GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

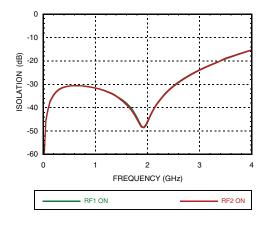
Insertion Loss



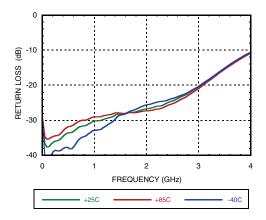
Isolation Between RFC & RF1/RF2



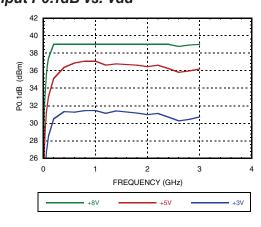
RF1 to RF2 Isolation



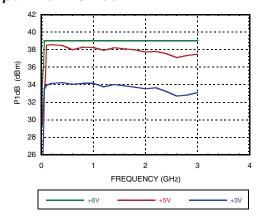
Return Loss



Input P0.1dB vs. Vdd



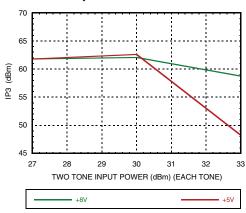
Input P1dB vs. Vdd



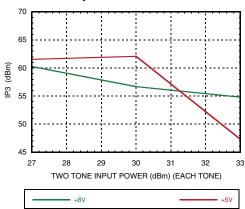


GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

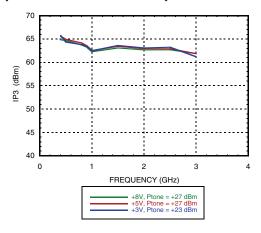
Input IP3 vs. Input Power @ 900 MHz



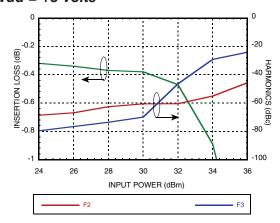
Input IP3 vs. Input Power @ 1900 MHz



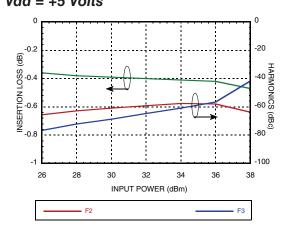
Input Third Order Intercept



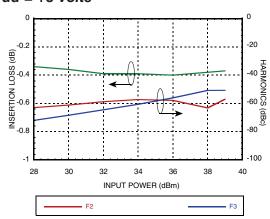
2nd & 3rd Harmonics @ 900 MHz Vdd = +3 Volts



2nd & 3rd Harmonics @ 900 MHz Vdd = +5 Volts



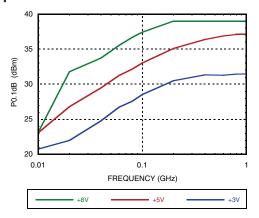
2nd & 3rd Harmonics @ 900 MHz Vdd = +8 Volts



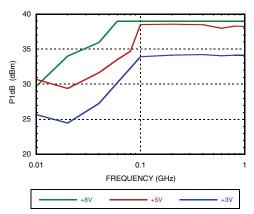


GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

Input P0.1dB vs. Vdd



Input P1dB vs. Vdd



Absolute Maximum Ratings

Max. Input Power $V_{dd} = 0/+8V$	0.5 - 2.5 GHz	39 dBm	
Bias Voltage Range (Vdd)		-0.2 to +10 Vdc	
Control Voltage Range (A & B)		-0.2 to +Vdd Vdc	
Channel Temperature		150 °C	
Continuous Pdiss (T= +85 °C) (derate 10 mW/°C above 85 °C)		0.775W	
Thermal Resistance		83.9 °C/W	
Storage Temperature		-65 to +150 °C	
Operating Temperature		-40 to +85 °C	
ESD Sensitivity (HBM) Class 1/		Class 1A	

DC Blocks are required at ports RFC, RF1 and RF2

Bias Voltage & Current

Vdd (Vdc)	Typical Idd (μA)
+3	0.5
+5	1
+8	20

Control Voltages

	State	Bias Condition
	Low	0 to +0.2 Vdc @ 1 μA Typical
High		Vdd ± 0.2 Vdc @ 1 µA Typical

ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

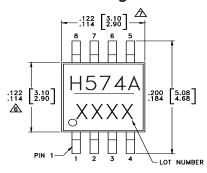
Truth Table

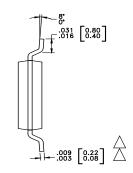
Control Input (Vctl)		Signal P	ath State
Α	В	RFC to RF1	RFC to RF2
High	Low	Off	On
Low	High	On	Off

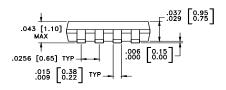


GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

Outline Drawing







NOTES:

- 1. PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
- 2. LEAD MATERIAL: COPPER ALLOY.
- 3. LEAD PLATING: 100% MATTE TIN.
- 4. DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 5. CHARACTERS TO BE HELVETICA MEDIUM, .030 HIGH, LASER OR WHITE INK, LOCATED APPROXIMATELY AS SHOWN.
- A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
 - 8. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC574AMS8E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [1]	<u>H574A</u> XXXX

^[1] Max peak reflow temperature of 260 $^{\circ}\text{C}$

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	А	See truth table and control voltage table.	○————————————————————————————————————
2	В	See truth table and control voltage table.	c
3, 5, 8	RFC, RF1, RF2	This pin is DC coupled and matched to 50 Ohm. Blocking capacitors are required.	
4	Vdd	Supply Voltage.	
6, 7	GND	This pin must be connected to RF/DC ground.	GND =

^{[2] 4-}Digit lot number XXXX

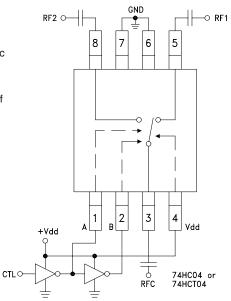


GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

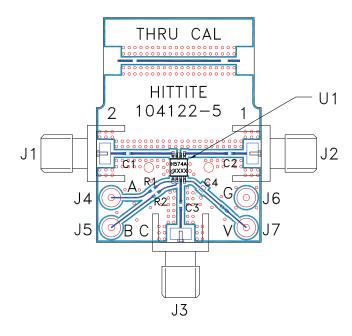
Typical Application Circuit

Notes:

- 1. Set logic gate and switch Vdd = +3V to +5V and use HCT series logic to provide a TTL driver interface.
- Control inputs A/B can be driven directly with CMOS logic (HC) with Vdd of +3 to +8 Volts applied to the CMOS logic gates and to pin 4 of the RF switch.
- 3. DC Blocking capacitors are required for each RF port as shown. Capacitor value determines lowest frequency of operation.
- Highest RF signal power capability is achieved with Vdd set to +8V.
 The switch will operate properly (but at lower RF power capability) at bias voltages down to +3V.



Evaluation Circuit Board



List of Materials for Evaluation PCB EV1HMC574AMS8 [1]

Item	Description
J1 - J3	PCB Mount SMA RF Connector
J4 - J7	DC Pin
C1 - C3	100 pF capacitor, 0402 Pkg.
C4	10,000 pF capacitor, 0603 Pkg.
R1, R2	100 Ohm resistor, 0402 Pkg.
U1	HMC574AMS8E T/R Switch
PCB [2]	104122 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB $\,$

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 Ohm impedance and the package ground leads and package bottom should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Analog Devices Inc upon request.